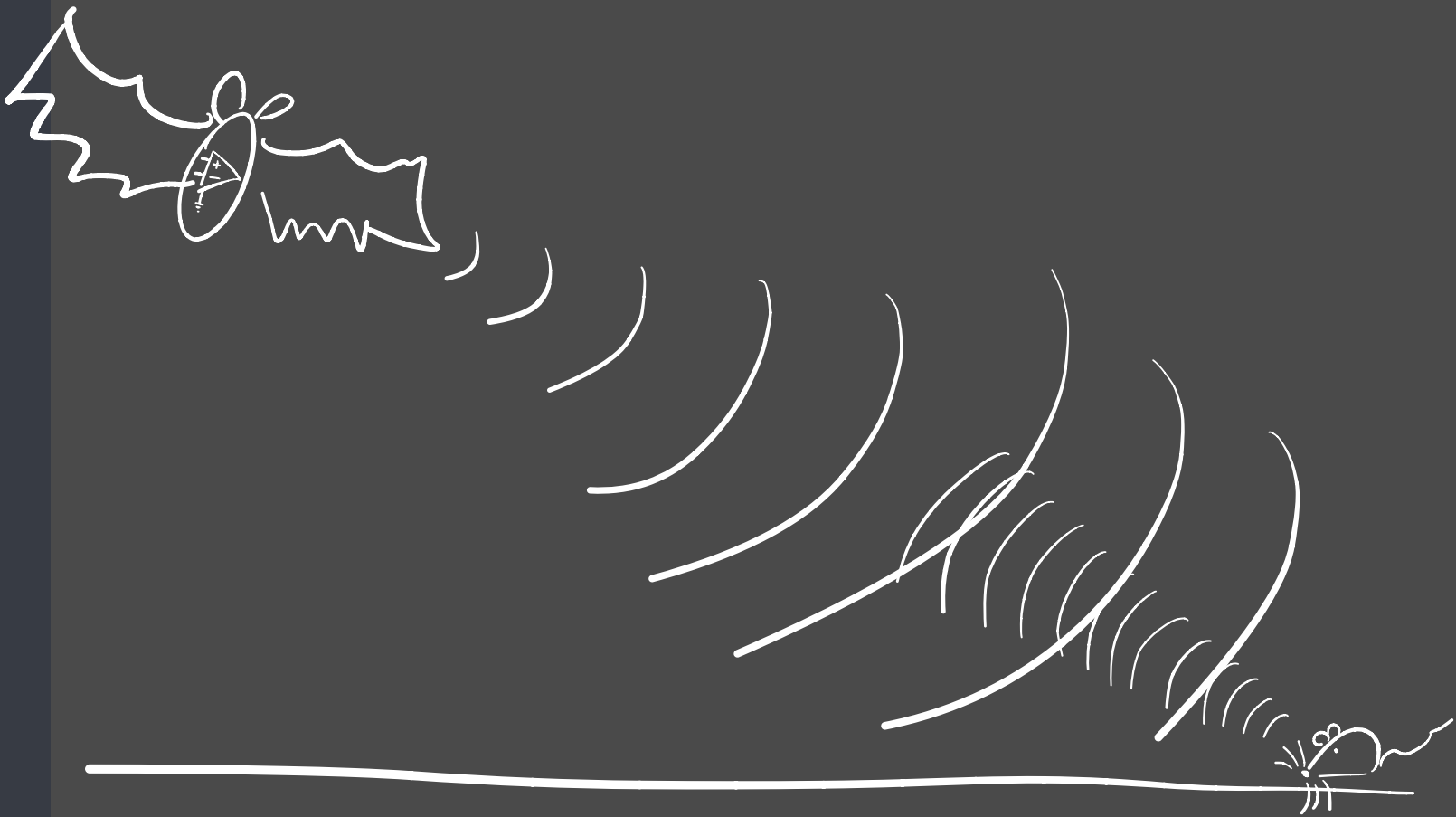


# Virtual-Spin $\gamma$ C

Fast single-charge sensing

1W ce RF quantum point contact

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Miguel  $\gamma$ .C.

May 19<sup>th</sup>, 2020

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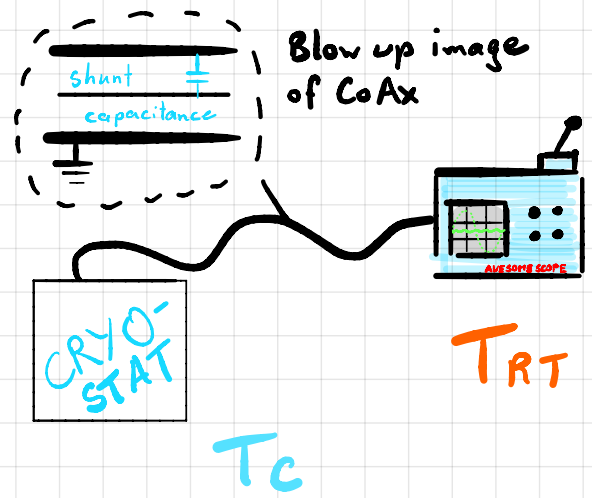
# INTRO

• SETs & QPCs → sensitive & non-invasive

• BUT, speed of operation limited by large  $\tau = RC$

and shunt capacitance of wire

$$\tau = RC \begin{cases} R > 50 \text{ k}\Omega \\ C \approx 100 \text{ pF} \end{cases}$$



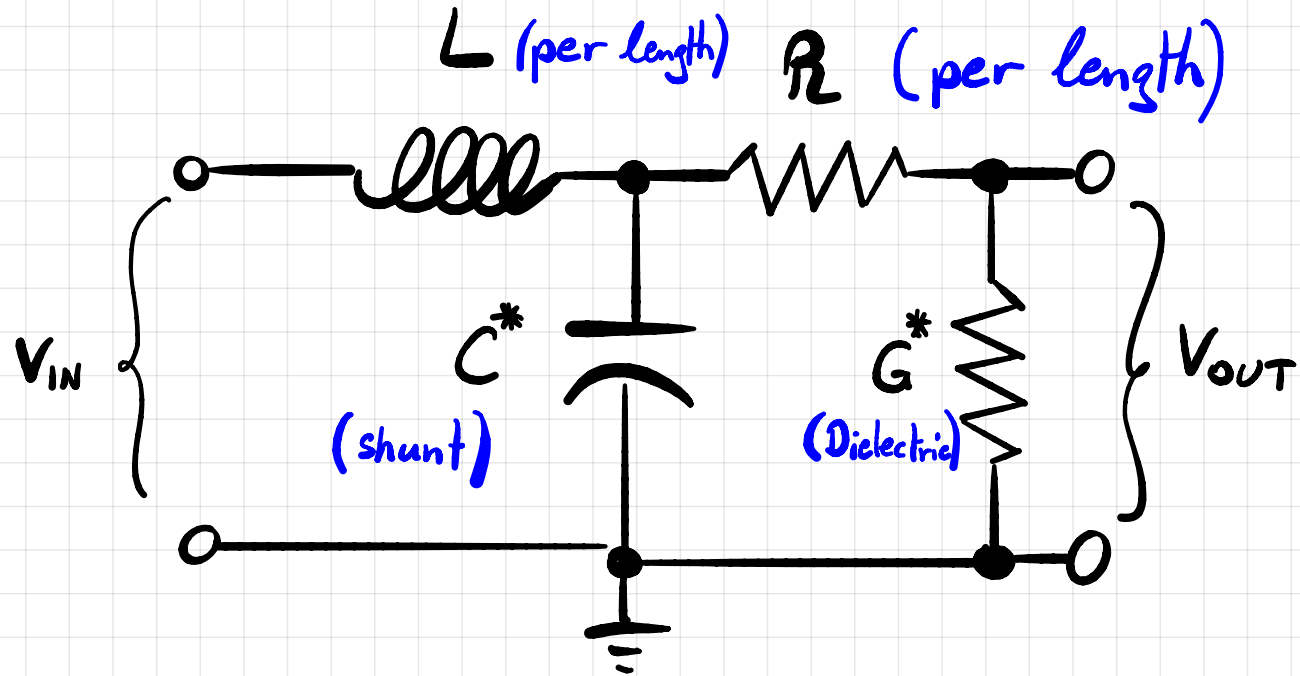
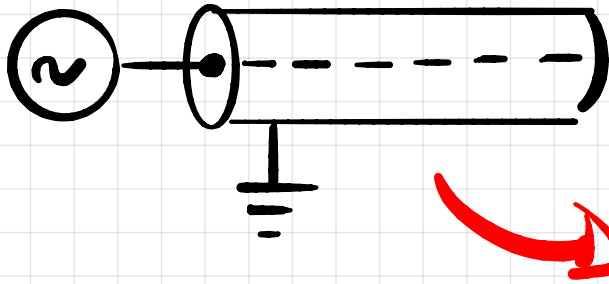
→ Plays large role in DC meas.

• Solve this issue w/ impedance matching network toward  $typ. Z_0 = 50 \Omega$  of trans. line. (AC)

• Also desire high  $f \rightarrow 1/f$  noise  $\xrightarrow{(f \gg 1)}$   $\ominus$  (AC)

# Quick detour „The TL-model“ 2/9

Regular CoAx:



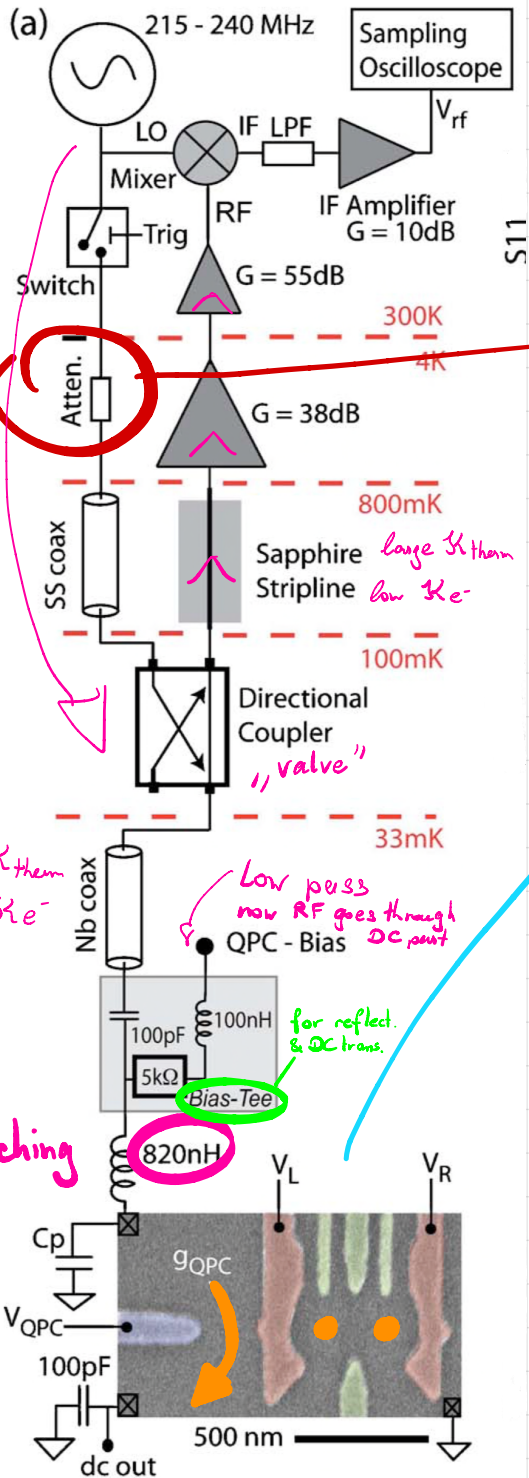
$$\tilde{Z}_0 = \sqrt{\frac{R + i\omega L}{G + i\omega C}} \rightsquigarrow \tilde{Z}_0 = \sqrt{\frac{L}{C}} \quad \text{lossless line}$$

(what we mainly care about in AC, + simpler)

Attempt to match this  $\tilde{Z}_0$  by choosing an  $L'$  down @ sample s.t. together w/  $C'$  from bonds the resulting LC-circ. matches  $\tilde{Z}_0$ .

Reflection:  $\Gamma = \frac{\tilde{Z}' - \tilde{Z}_0}{\tilde{Z}' + \tilde{Z}_0} \xrightarrow{(\tilde{Z}' \rightarrow \tilde{Z}_0)} 0$  changes of  $\tilde{Z}'$  coming from sample, manifest in reflected signal.

# Device



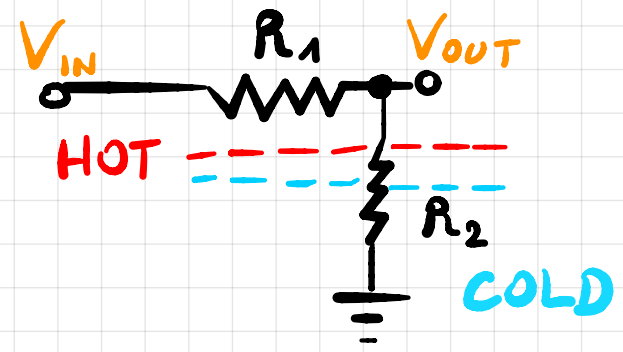
attenuators: i) better SNR

ii) thermalization through electrons

$$V_{OUT} = V_{IN} \frac{R_2}{R_1 + R_2}$$

$$R_1 > R_2$$

$$T_e = 120 \text{ mK}$$



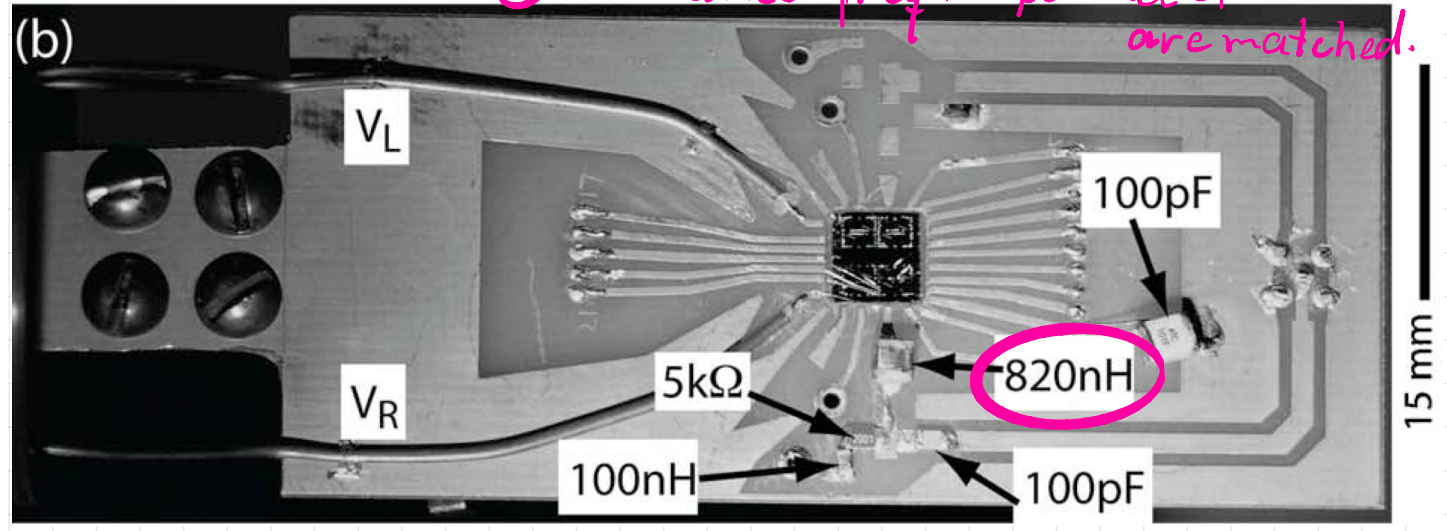
changes in gapc modulate  $\Gamma$  from matching circuit

@ resonance freq. impedance of LC & TL are matched.

low  $R_{th}$  them high  $R_{e^-}$

low pers now RF goes through DC point

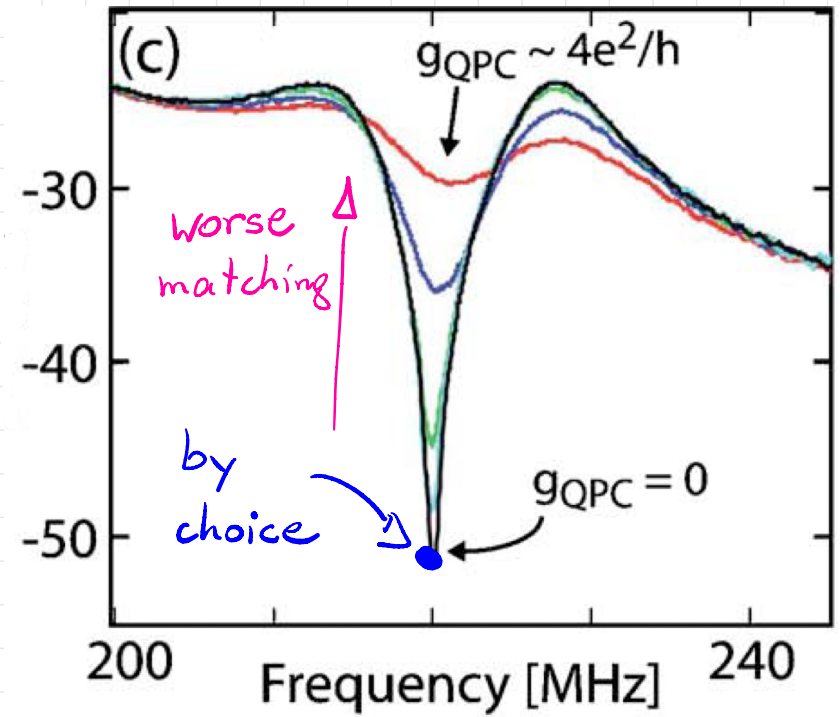
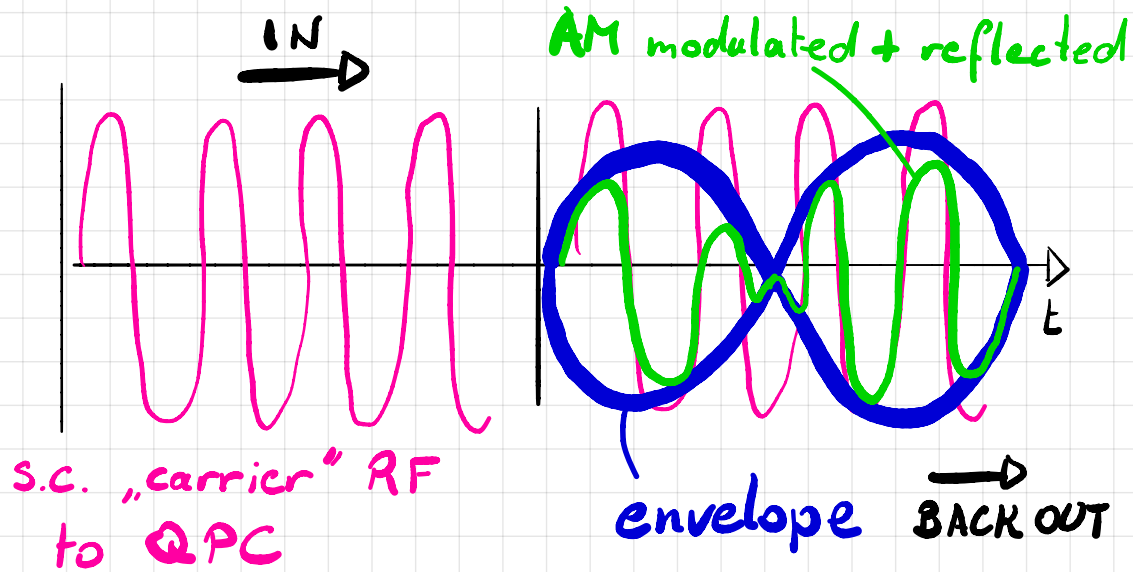
for matching



# Characteristics

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- matching via chip inductor  
820nH & parasitic C from bonds  $\sim 0.63$  pF.  
 $\Delta g_{QPC} \Rightarrow \Delta \Gamma$  (modulates reflected power)



② is demodulated on local oscillator LO @ RT to get inter mediate freq., then low pass filtered & amplified to yield  $V_{RF} \propto g_{QPC}$ .

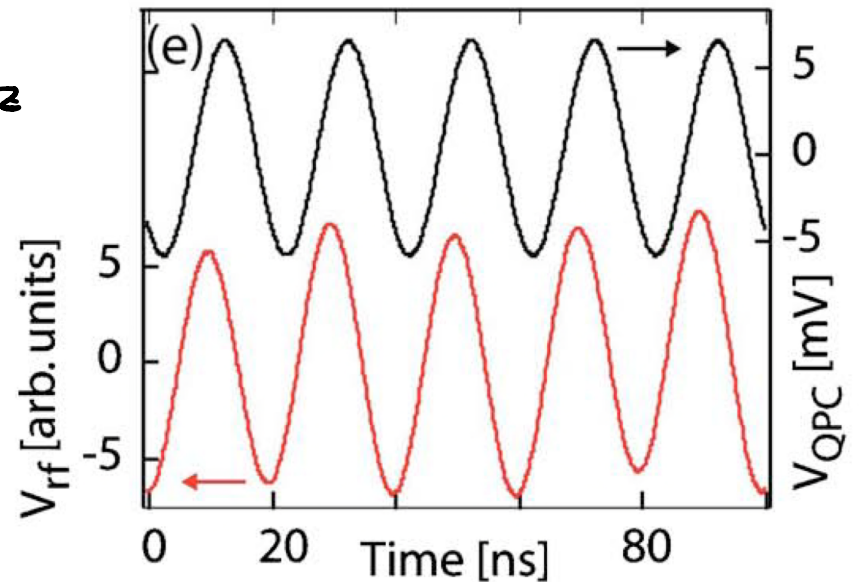
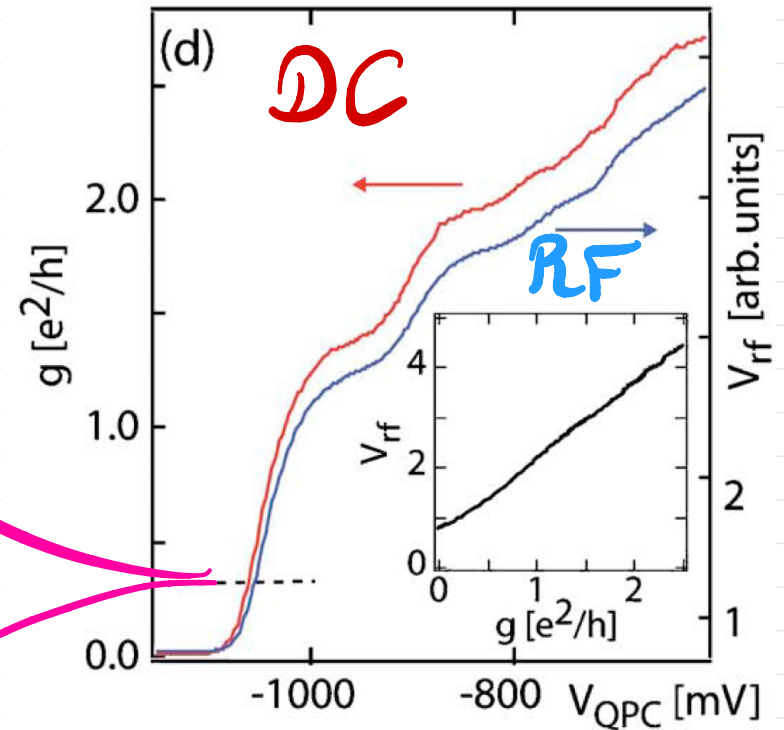
- Simultaneous RF & DC

tuned  $V_{QPC}$   
here for max  
sensitivity

- For  $g_{QPC} > e^2/h$  &  $L_{match} = 560 \text{ nH}$

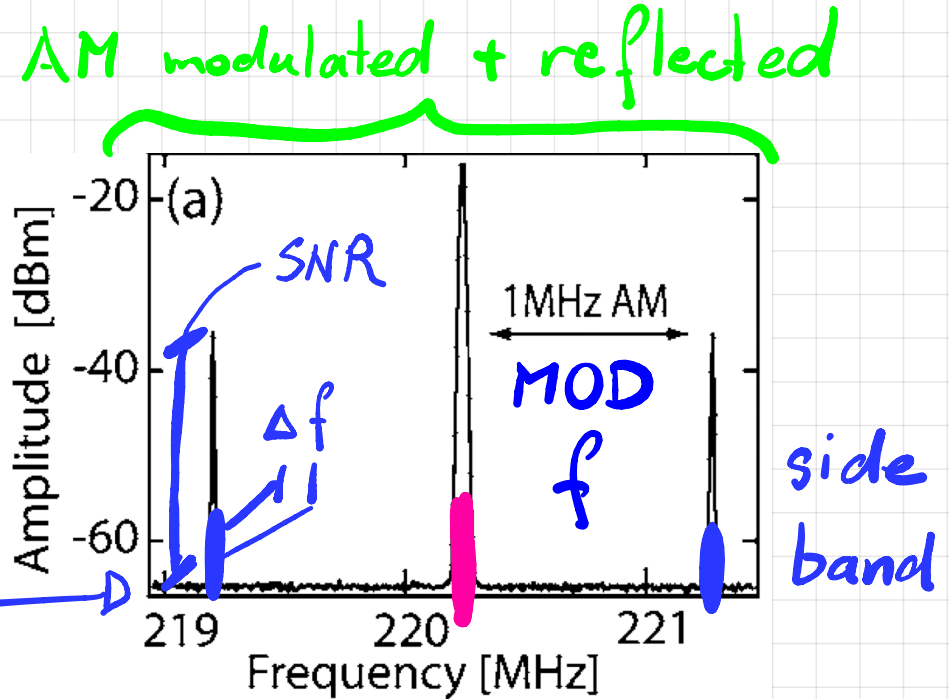
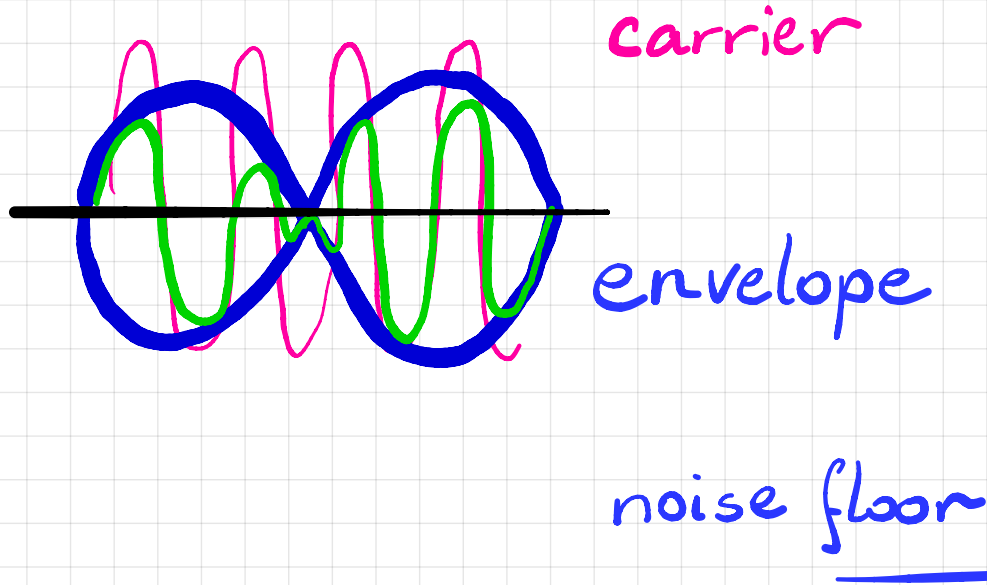
→ under coupled regime. Bandwidth  $\sim 100 \text{ MHz}$   
determined by rise time of  $V_{RF}$  in  
response to  $50 \text{ MHz}$  bias on gate.

2 How do I see this?

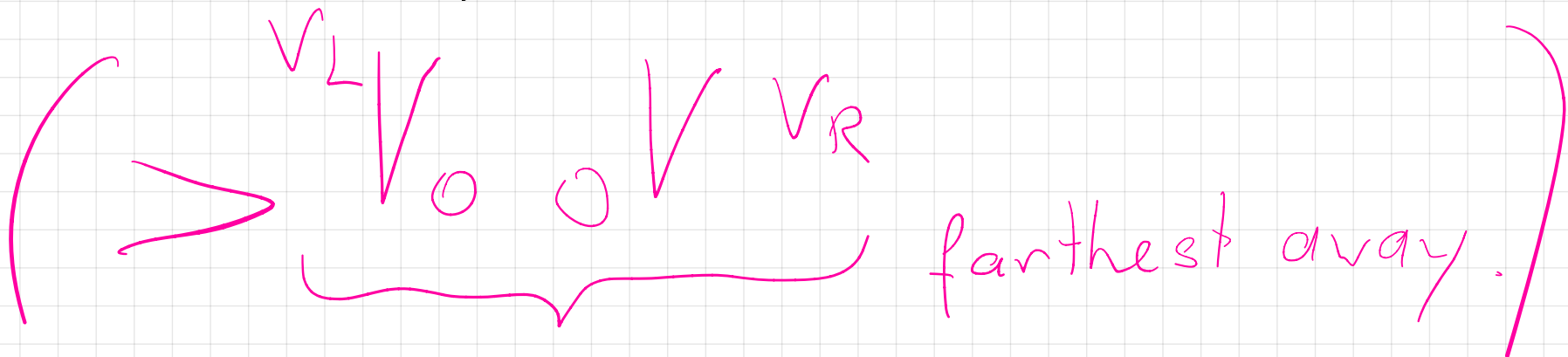


# Sensitivity

- Apply  $V_R = 0.7 \text{ mV}$  @  $1 \text{ MHz}$   $\rightsquigarrow$  modulate  $\Delta g_{\text{QPC}} \sim 0.018 e^2/h$



- Sensitivity allows for  $\Delta g_{\text{QPC}} = 0.01 e^2/h$  with  $\text{SNR} = 1$  in  $\tau_{\text{int}} = 0.5 \mu\text{s}$ .



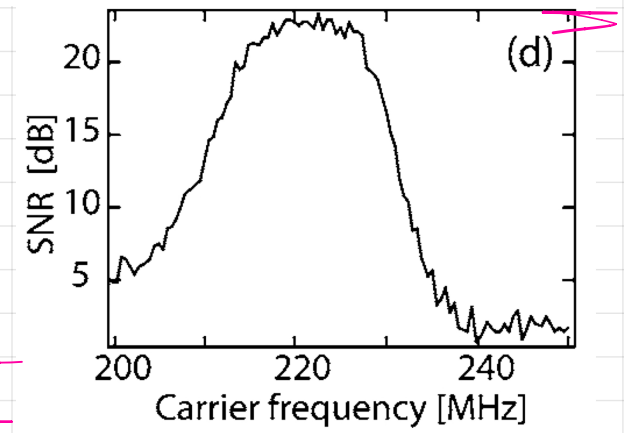
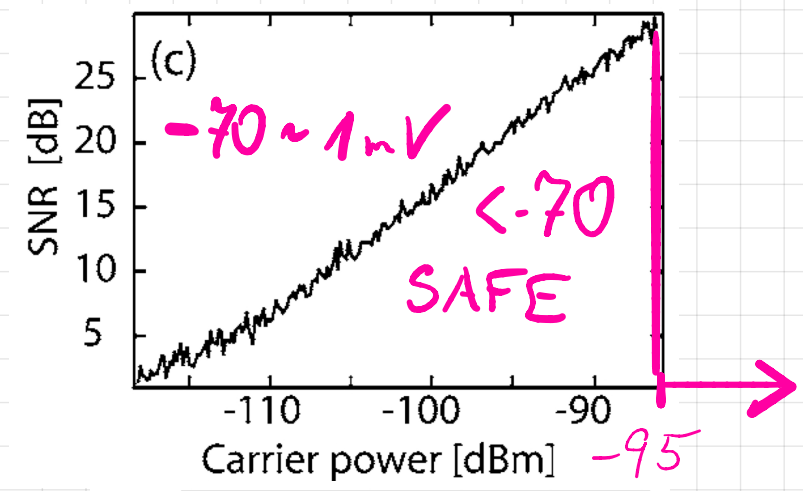
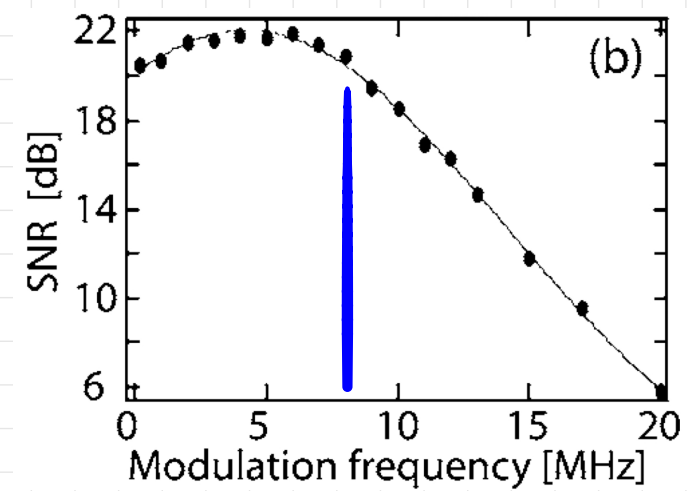
# Limitations

- $f \approx 8\text{MHz}$ ,  $Q \sim 15$   
limits the sensitivity. ( $Q = \frac{f_r}{\Delta f}$ )

- SNR  $\uparrow$  w  $P_{\text{CARRIER}} \uparrow$   
limit set by E-scale of  
AD subband spacing ( $\sim \text{mV}$ ).

- @  $-75\text{dBm}$  upper side  
band SNR (What is "consistent"  
with Fig 1c?)

Quick Math:  $-75 - 20 = -95$

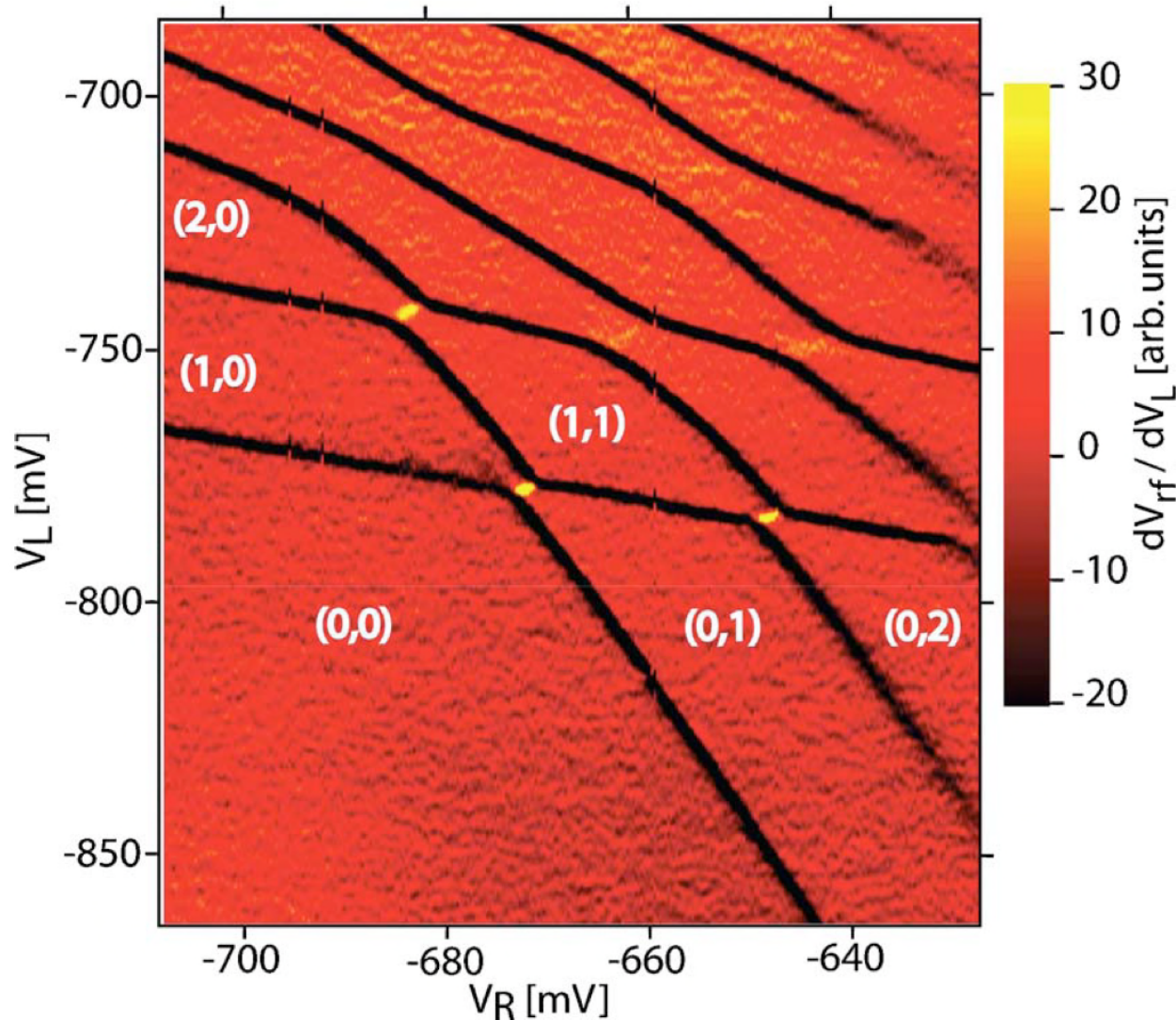




# Result

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- Biased QPC @  $0.3 e^2/h$   $\rightarrow$  very sensitive.  
Below,  $V_{RF}$  as func of  $V_R$  &  $V_L$ . 32 avg p.p.



# Challenges & Improvements

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- RF on QPC : i) back-action (shot noise) can drive unwanted transitions
- @ high RF carrier power  $\rightarrow$  distortion of CSD (heat).
- circumvent problems by using a solid-state RF switch.
- Q fac sets 50ns ? for QPC to enter meas.
- After delay of 1 $\mu$ s meas is triggered.
- SNR  $\sim 4$

